12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20130628004
Transfer of the TPD4E101DPWR device (Vertical Diode-BD process node) to CFAB
Facility Change Notification / Sample Request

Date: 6/28/2013
To: MOUSER PCN

Dear Customer:

In January, 2012, TI announced plans to close two older 6-inch manufacturing facilities in Hiji, Japan and Houston, Texas. This change announces the fab transfer of the TPD4E101DPWR device (Vertical Diode-Bi-Directional process node). The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days to ensure you can complete your evaluation and product transfer to the new site can be completed prior to the fab closure.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Manager (PCN_ww_admin_team@list.ti.com).

Sincerely,

PCN Team
SC Business Services
Phone: +1(214) 480-6037
Fax: +1(214) 480-6659

20130628004
Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
TPD4E101DPWR	null

Technical details of this Product Change follow on the next page(s).

PCN Number:	20130628004	PCN Date:	06/28/2013
Title:	Transfer of the TPD4E101DPWR device (Vertical Diode-BD process node) to CFAB Facility		
Customer Contact:	PCN Manager	Phone: +1(214)480-6037	Dept: Quality Services
Proposed 1st Ship Date:	09/28/2013	Estimated Sample Availability:	Date available upon sample request

Change Type:

☐	Assembly Site	☐	Assembly Process	☐	Assembly Materials
☐	Design	☐	Electrical Specification	☐	Mechanical Specification
☐	Test Site	☐	Packing/Shipping/Labeling	☐	Test Process
☐	Wafer Bump Site	☐	Wafer Bump Material	☐	Wafer Bump Process
☒	Wafer Fab Site	☐	Wafer Fab Materials	☒	Wafer Fab Process

PCN Details

Description of Change:

This change notification is to announce the transfer of the TPD4E101DPWR device (Vertical Diode – Bi-Directional process node) from HIJI to the CFAB facility. This will also include a wafer diameter change from 6” to 8”.

Current	New
Site, process, wafer dia.	**Site, process, wafer dia.**
HIJI/ VD-BD, 150mm	**CFAB/ VD-BD, 200mm**

Reason for Change:

Continuity of Supply. HIJI site shutdown.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Current

Chip Site	Chip site code (20L)	Chip country code (21L)
HIJI	HIJ	JPN

New

Chip Site	**Chip site code (20L)**	**Chip country code (21L)**
CFAB	**CU3**	**CHN**

Fab Identification on Topside Symbol Marking:

Current	HIJI	A1
New	**CFAB**	**A2**

Sample product shipping label (not actual product label)

Product Affected:
TPD4E101DPWR

Qualification Data (Approved 6/11/2013)

This qualification has been developed for the validation of this change. The qualification data will validate that the proposed change meets the applicable released technical specifications.

Qual Vehicle: TPD4E101DPWR

Wafer Fab Site:	CFAB	Metallization:	AlCuTiW
Wafer Fab Process:	VD	Wafer Diameter:	200mm

Qualification: ☐ **Plan** ☒ **Test Results**

Reliability Test	Conditions	Sample Size/Fails Lot#1	Lot#2	Lot#3
HTOL High Temp Op Life	150C (300 Hrs)	77/0	77/0	77/0
Electrical Characterization	-	Pass	-	-
**High Temp. Storage Bake	170C (420 Hrs)[note 1]	77/0	77/0	77/0
**Biased HAST	130C/85%RH (96 Hrs)	77/0	77/0	77/0
**Autoclave 121C	121C, 2 atm (96 Hrs)	77/0	77/0	77/0
**Temperature Cycle	-65C/+150C (500 Cycles)	77/0	77/0	77/0
ESD CDM	500V	3/0	3/0	3/0
ESD HBM	2000V	3/0	3/0	3/0
Latch-up [note 2]	-	N/A	N/A	N/A

**Preconditioning: Level 1-260C

Note 1: 420hrs @ 170C is equivalent to 1000hrs @ 150C storage life bake, based on activation energy of 0.7eV.

Note 2: Latch-up is a power up test to check for current paths from I/O pins to power. The TPD4E101DPWR is a diode device with no power pin-with no concern of an SCR, therefore latch-up testing is not a required test for this qualification.

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com